Paul koenraad

List of Publications by Year
in descending order

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228 papers	5,736 citations	76326 40 h-index	110387 64 g-index
232 all docs	232 docs citations	232 times ranked	4719 citing authors

#	Article	IF	Citations
1	Study of Size, Shape, and Etch pit formation in InAs/InP Droplet Epitaxy Quantum Dots. Nanotechnology, 2022, 33, 305705.	2.6	3
2	Control of Morphology and Substrate Etching in InAs/InP Droplet Epitaxy Quantum Dots for Single and Entangled Photon Emitters. ACS Applied Nano Materials, 2022, 5, 8070-8079.	5.0	6
3	Atomic-Scale Characterization of Droplet Epitaxy Quantum Dots. Nanomaterials, 2021, 11, 85.	4.1	20
4	Structural and compositional analysis of (InGa)(AsSb)/GaAs/GaP Stranskiâ€“Krastanov quantum dots. Light: Science and Applications, 2021, 10, 125.	16.6	14
5	Atomic-scale study of Si-doped AlAs by cross-sectional scanning tunneling microscopy and density functional theory. Physical Review B, 2021, 104, .	3.2	4
6	Highly Tensile-Strained Self-Assembled Ge Quantum Dots on InP Substrates for Integrated Light Sources. ACS Applied Nano Materials, 2021, 4, 897-906.	5.0	12
7	FrÃ¶hlich interaction dominated by a single phonon mode in CsPbBr3. Nature Communications, 2021, 12, 5844.	12.8	34
8	Design and Characterization of a Sharp GaAs/Zn(Mn)Se Heterovalent Interface: A Sub-Nanometer Scale View. Nanomaterials, 2020, 10, 1315.	4.1	0
9	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi mathvariant="normal">N</mml:mi><mml:mtext>â^</mml:mtext><mml:mi>n</mml:mi><mml:mi mathvariant="normal">H</mml:mi></mml:math> complexes in GaAs studied at the atomic scale by cross-sectional scanning tunneling microscopy. Physical Review B, 2020, 102, .	3.2	4
10	Probing the local electronic structure of isovalent Bi atoms in InP. Physical Review B, 2020, 101, .	3.2	2
11	Cross-sectional scanning tunneling microscopy of InAs/GaAs(001) submonolayer quantum dots. Physical Review Materials, 2020, 4, .	2.4	14
12	Composition analysis and transition energies of ultrathin Sn-rich GeSn quantum wells. Physical Review Materials, 2020, 4, .	2.4	10
13	Structural Properties of Bi Containing InP Films Explored by Cross-Sectional Scanning. Springer Series in Materials Science, 2019, , 215-229.	0.6	0
14	Active tuning of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> -tensor in InGaAs/GaAs quantum dots via strain. Physical Review B, 2019, 99, .	3.2	9
15	Te incorporation and activation as <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type dopant in self-catalyzed GaAs nanowires. Physical Review Materials, 2019, 3, .	2.4	17
16	Structural and electronic properties of isovalent boron atoms in GaAs. Journal of Applied Physics, 2018, 123, 161589.	2.5	6
17	Size and shape tunability of self-assembled InAs/GaAs nanostructures through the capping rate. Applied Surface Science, 2018, 444, 260-266.	6.1	26
18	Micro and Nanoscale Characterization of Complex Multilayer-Structured White Etching Layer in Rails. Metals, 2018, 8, 749.	2.3	17

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19	Self-organized Quantum Rings: Physical Characterization and Theoretical Modeling. Nanoscience and Technology, 2018, , 91-120.	1.5	0
20	Direct Probing of the Dielectric Scavenging-Layer Interface in Oxide Filamentary-Based Valence Change Memory. ACS Applied Materials & Interfaces, 2017, 9, 10820-10824.	8.0	50
21	Boosting Hole Mobility in Coherently Strained [110]-Oriented Geâ€“Si Coreâ€“Shell Nanowires. Nano Letters, 2017, 17, 2259-2264.	9.1	51
22	Growth and Optical Properties of Direct Band Gap Ge/Ge_{0.87}Sn_{0.13} Core/Shell Nanowire Arrays. Nano Letters, 2017, 17, 1538-1544.	9.1	72
23	Atom-by-Atom Analysis of Semiconductor Nanowires with Parts Per Million Sensitivity. Nano Letters, 2017, 17, 599-605.	9.1	35
24	Strong Carrierâ€“Phonon Coupling in Lead Halide Perovskite Nanocrystals. ACS Nano, 2017, 11, 11024-11030.	14.6	119
25	Observation of the symmetry of core states of a single Fe impurity in GaAs. Physical Review B, 2017, 96, .	3.2	3
26	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. Physical Review B, 2017, 96, .	3.2	8
27	Exploration of Doped Semiconductors at the Atomic Scale. Microscopy and Microanalysis, 2017, 23, 670-671.	0.4	0
28	Incorporation of Bi atoms in InP studied at the atomic scale by cross-sectional scanning tunneling microscopy. Physical Review Materials, 2017, 1, .	2.4	11
29	Bulk AlInAs on InP(111) as a novel material system for pure single photon emission. Optics Express, 2016, 24, 23198.	3.4	10
30	An atomic scale study of surface termination and digital alloy growth in InGaAs/AlAsSb multi-quantum wells. Journal of Physics Condensed Matter, 2016, 28, 284002.	1.8	3
31	Strain-induced<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>-factor tuning in single InGaAs/GaAs quantum dots. Physical Review B, 2016, 94, .	3.2	15
32	Optical study of the band structure of wurtzite GaP nanowires. Journal of Applied Physics, 2016, 120, .	2.5	34
33	Dispersion of the electron g factor anisotropy in InAs/InP self-assembled quantum dots. Journal of Applied Physics, 2016, 120, 084301.	2.5	5
34	Electronic wave functions and optical transitions in (In,Ga)As/GaP quantum dots. Physical Review B, 2016, 94, .	3.2	10
35	Optical orientation of spins in GaAs:Mn/AlGaAs quantum wells via impurity-to-band excitation. Physical Review B, 2016, 94, .	3.2	5
36	Optical spectroscopy of single beryllium acceptors in GaAs/AlGaAs quantum well. Physical Review B, 2016, 94, .	3.2	3

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37	High-purity 3D nano-objects grown by focused-electron-beam induced deposition. Nanotechnology, 2016, 27, 355301.	2.6	34
38	Scanning tunneling microscopy contrast of isovalent impurities on the GaAs (110) surface explained with a geometrical model. Physical Review B, 2016, 93, .	3.2	10
39	Influence of growth conditions on the performance of InP nanowire solar cells. Nanotechnology, 2016, 27, 454003.	2.6	10
40	Pâ€“N Junctions in Ultrathin Topological Insulator Sb₂Te₃/Bi₂Te₃ Heterostructures Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 2057-2061.	3.0	36
41	Anisotropy of electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>tensors of quantum dots: An intuitive picture based on spin-correlated orbital currents. Physical Review B, 2016, 93, .	3.2	25
42	Precise shape engineering of epitaxial quantum dots by growth kinetics. Physical Review B, 2015, 92, .	3.2	34
43	Size-dependent line broadening in the emission spectra of single GaAs quantum dots: Impact of surface charge on spectral diffusion. Physical Review B, 2015, 92, .	3.2	33
44	Mn doped InSb studied at the atomic scale by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2015, 107, .	3.3	4
45	Model for the light-induced magnetization in singly charged quantum dots. Physical Review B, 2015, 91, .	3.2	1
46	Bistable Si dopants in the GaAs (1â€‰1â€‰0) surface. Journal of Physics Condensed Matter, 2015, 27, 154201.	1.8	4
47	Suppressing Segregation in Highly Phosphorus Doped Silicon Monolayers. ACS Nano, 2015, 9, 12537-12541.	14.6	36
48	Structural, electronic, and magnetic properties of single MnAs nanoclusters in GaAs. Applied Physics Letters, 2014, 105, 232405.	3.3	2
49	Photoluminescence studies of individual and few GaSb/GaAs quantum rings. AIP Advances, 2014, 4, .	1.3	9
50	Height stabilization of GaSb/GaAs quantum dots by Al-rich capping. APL Materials, 2014, 2, 096111.	5.1	9
51	InAs quantum dot morphology after capping with In, N, Sb alloyed thin films. Applied Physics Letters, 2014, 104, .	3.3	28
52	Tunable switching dynamics of a single Si dopant in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>GaAs</mml:mi><mml:mo>(</mml:mo><mml:mn>110</mml:mn></m Physical Review B, 2014, 90, .	3.2	5
53	Composition profiling of GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2014, 105, .	3.3	13
54	Geometric and compositional influences on spin-orbit induced circulating currents in nanostructures. Physical Review B, 2014, 90, .	3.2	9

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55	Volmerâ€“Weber InAs quantum dot formation on InP (113)B substrates under the surfactant effect of Sb. Applied Physics Letters, 2014, 105, 033113.	3.3	1
56	Spin-Orbit-Induced Circulating Currents in a Semiconductor Nanostructure. Physical Review Letters, 2014, 112, 187201.	7.8	20
57	Height control of self-assembled quantum dots by strain engineering during capping. Applied Physics Letters, 2014, 105, 143104.	3.3	4
58	Self-organized Quantum Rings: Physical Characterization and Theoretical Modeling. Nanoscience and Technology, 2014, , 83-105.	1.5	2
59	Aharonov-Bohm oscillations in the magnetic moment of multielectron randomly doped semiconductor cylindrical core-shell nanowires. Physical Review B, 2013, 87, .	3.2	7
60	Morphological Description of Ultraâ€Smooth Organoâ€Silicone Layers Synthesized Using Atmospheric Pressure Dielectric Barrier Discharge Assisted PECVD. Plasma Processes and Polymers, 2013, 10, 313-319.	3.0	13
61	The structural, electronic and optical properties of GaSb/GaAs nanostructures for charge-based memory. Journal Physics D: Applied Physics, 2013, 46, 264001.	2.8	44
62	Blueshifts of the emission energy in type-II quantum dot and quantum ring nanostructures. Journal of Applied Physics, 2013, 114, 073519.	2.5	24
63	Core-state manipulation of single Fe impurities in GaAs with a scanning tunneling microscope. Physical Review B, 2013, 87, .	3.2	18
64	The disintegration of GaSb/GaAs nanostructures upon capping. Applied Physics Letters, 2013, 102, .	3.3	26
65	Magnetic anisotropy of single Mn acceptors in GaAs in an external magnetic field. Physical Review B, 2013, 88, .	3.2	5
66	Laser and voltage manipulation of bistable Si dopants in the GaAs (110) surface. Physical Review B, 2013, 87, .	3.2	8
67	Long wavelength (>1.55â€‰Î¼m) room temperature emission and anomalous structural properties of InAs/GaAs quantum dots obtained by conversion of In nanocrystals. Applied Physics Letters, 2013, 102, 073103.	3.3	5
68	Analysis of the modified optical properties and band structure of GaAs1â^'xSbx-capped InAs/GaAs quantum dots. Journal of Applied Physics, 2012, 112, .	2.5	33
69	Scanning tunneling microscopy reveals LiMnAs is a room temperature anti-ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, 112107.	3.3	11
70	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>g</mml:mi></mml:math>factors and diamagnetic coefficients of electrons, holes, and excitons in InAs/InP quantum dots. Physical Review B, 2012, 85, .	3.2	51
71	Atomically resolved study of the morphology change of InAs/GaAs quantum dot layers induced by rapid thermal annealing. Applied Physics Letters, 2012, 101, .	3.3	14
72	Linking structural and electronic properties of high-purity self-assembled GaSb/GaAs quantum dots. Physical Review B, 2012, 86, .	3.2	35

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73	Optical observation of single-carrier charging in type-II quantum ring ensembles. Applied Physics Letters, 2012, 100, .	3.3	41
74	GaSb/GaAs quantum dot formation and demolition studied with cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2012, 100, .	3.3	40
75	Kinetic Monte Carlo simulations and cross-sectional scanning tunneling microscopy as tools to investigate the heteroepitaxial capping of self-assembled quantum dots. Physical Review B, 2012, 85, .	3.2	12
76	Surface Dynamics of SiO₂â€like Films on Polymers Grown by DBD Assisted CVD at Atmospheric Pressure. Plasma Processes and Polymers, 2012, 9, 1194-1207.	3.0	15
77	Highly nonlinear excitonic Zeeman spin splitting in composition-engineered artificial atoms. Physical Review B, 2012, 85, .	3.2	24
78	Challenges in cross-sectional scanning tunneling microscopy on semiconductors. Semiconductor Science and Technology, 2011, 26, 064001.	2.0	8
79	Short-period (Ga,Mn)As/(Al,Ga)As multilayer structures studied by cross-sectional scanning tunneling microscopy. Physical Review B, 2011, 84, .	3.2	2
80	Bistable Charge Configuration of Donor Systems near the GaAs(110) Surfaces. Nano Letters, 2011, 11, 3538-3542.	9.1	14
81	Composition profiling of InAs quantum dots and wetting layers by atom probe tomography and cross-sectional scanning tunneling microscopy. Physical Review B, 2011, 83, .	3.2	46
82	Single dopants in semiconductors. Nature Materials, 2011, 10, 91-100.	27.5	385
83	Shape and size control of InAs/InP (113)B quantum dots by Sb deposition during the capping procedure. Nanotechnology, 2011, 22, 055703.	2.6	6
84	Bistable behavior of silicon atoms in the (110) surface of gallium arsenide. Physical Review B, 2011, 84, .	3.2	19
85	Single Si dopants in GaAs studied by scanning tunneling microscopy and spectroscopy. Physical Review B, 2011, 84, .	3.2	24
86	Observation and explanation of strong electrically tunable exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>g</mml:mi></mml:mrow></mml:math>factors in composition engineered In(Ga)As quantum dots. Physical Review B, 2011, 83, .	3.2	34
87	Structural atomic-scale analysis of GaAs/AlGaAs quantum wires and quantum dots grown by droplet epitaxy on a (311)A substrate. Applied Physics Letters, 2011, 98, 193112.	3.3	14
88	Shape control of quantum dots studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2011, 109, 102413.	2.5	13
89	An atomic scale study on the effect of Sb during capping of MBE grown IIIâ€“V semiconductor QDs. Semiconductor Science and Technology, 2011, 26, 064007.	2.0	28
90	Self-Assembly of GaAs Quantum Wires Grown on (311)A Substrates by Droplet Epitaxy. Applied Physics Express, 2011, 4, 055501.	2.4	6

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91	Size, strain and band offset engineering in GaAs(Sb)(N)-capped InAs quantum dots for 1.3 - 1.55 Î¼m emitters. , 2011, , .		1
92	Semiconductors Studied by Cross-sectional Scanning Tunneling Microscopy. Nanoscience and Technology, 2011, , 321-353.	1.5	2
93	Shape Control of QDs Studied by Cross-sectional Scanning Tunneling Microscopy. Journal of the Korean Physical Society, 2011, 58, 1244-1250.	0.7	1
94	Control of Strain in GaSbAs/InAs/GaAs Quantum Dots. Journal of Physics: Conference Series, 2010, 245, 012065.	0.4	3
95	Smooth and Selfâ€Similar SiO‹sub›2‹/sub›â€like Films on Polymers Synthesized in Rollâ€toâ€Roll Atmospheric Pressureâ€PECVD for Gas Diffusion Barrier Applications. Plasma Processes and Polymers, 2010, 7, 635-639.	3.0	51
96	Many-body exciton states in self-assembled quantum dots coupled to a Fermi sea. Nature Physics, 2010, 6, 534-538.	16.7	52
97	Effect of a lattice-matched GaAsSb capping layer on the structural properties of InAs/InGaAs/InP quantum dots. Journal of Applied Physics, 2010, 107, .	2.5	10
98	The role of dot height in determining exciton lifetimes in shallow InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	15
99	Enhanced binding energy of manganese acceptors close to the GaAs(110) surface. Physical Review B, 2010, 82, .	3.2	26
100	Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots. Physical Review B, 2010, 82, .	3.2	14
101	Generalized effective-mass theory of subsurface scanning tunneling microscopy: Application to cleaved quantum dots. Physical Review B, 2010, 82, .	3.2	11
102	Influence of the tip work function on scanning tunneling microscopy and spectroscopy on zinc doped GaAs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1086-1092.	1.2	11
103	Publisher's Note: Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots [Phys. Rev. B82, 235316 (2010)]. Physical Review B, 2010, 82, .	3.2	0
104	Atomic scale characterization of Mn doped InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	10
105	Surface Induced Asymmetry of Acceptor Wave Functions. Physical Review Letters, 2010, 104, 086404.	7.8	28
106	Achievement of InSb Quantum Dots on InP(100) Substrates. Japanese Journal of Applied Physics, 2010, 49, 060210.	1.5	1
107	An atomically resolved study of InGaAs quantum dot layers grown with an indium flush step. Nanotechnology, 2010, 21, 215705.	2.6	15
108	GaAsSb-capped InAs quantum dots: From enlarged quantum dot height to alloy fluctuations. Physical Review B, 2010, 81, .	3.2	86

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109	Atomic scale analysis of self assembled GaAs/AlGaAs quantum dots grown by droplet epitaxy. Applied Physics Letters, 2010, 96, .	3.3	60
110	Nanoscale Potential Fluctuations in (GaMn)As/GaAs Heterostructures: From Individual Ions to Charge Clusters and Electrostatic Quantum Dots. Nano Letters, 2010, 10, 4874-4879.	9.1	6
111	Structure of quantum dots as seen by excitonic spectroscopy versus structural characterization: Using theory to close the loop. Physical Review B, 2009, 80, .	3.2	45
112	Excitonic behavior in self-assembled InAs/GaAs quantum rings in high magnetic fields. Physical Review B, 2009, 80, .	3.2	33
113	Control of polarization and dipole moment in low-dimensional semiconductor nanostructures. Applied Physics Letters, 2009, 95, 221116.	3.3	14
114	Role of segregation in InAs/GaAs quantum dot structures capped with a GaAsSb strain-reduction layer. Physical Review B, 2009, 80, .	3.2	41
115	Size-dependent exciton<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>g</mml:mi></mml:math>factor in self-assembled InAs/InP quantum dots. Physical Review B, 2009, 79, .	3.2	30
116	High Quality SiO₂â€like Layers by Large Area Atmospheric Pressure Plasma Enhanced CVD: Deposition Process Studies by Surface Analysis. Plasma Processes and Polymers, 2009, 6, 693-702.	3.0	46
117	Simple and efficient scanning tunneling luminescence detection at low-temperature. Review of Scientific Instruments, 2009, 80, 123704.	1.3	15
118	Ellipsoidal InAs quantum dots observed by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2009, 94, 023107.	3.3	53
119	Enhanced Donor Binding Energy Close to a Semiconductor Surface. Physical Review Letters, 2009, 102, 166101.	7.8	57
120	The use of Abellâ€“Tersoff potentials in atomistic simulations of InGaAsSb/GaAs. Optical and Quantum Electronics, 2008, 40, 1143-1148.	3.3	2
121	Electron and exciton energy spectra in selfâ€assembled InGaAs/GaAs ringâ€like nanostructures. Physica Status Solidi (B): Basic Research, 2008, 245, 2657-2661.	1.5	18
122	Controlled Charge Switching on a Single Donor with a Scanning Tunneling Microscope. Physical Review Letters, 2008, 101, 076103.	7.8	150
123	Energy spectra and oscillatory magnetization of two-electron self-assembled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msu rings in GaAs. Physical Review B, 2008, 77, .	3.2	34
124	Atomically precise impurity identification and modification on the manganese doped GaAs(110) surface with scanning tunneling microscopy. Physical Review B, 2008, 78, .	3.2	42
125	The use of Abel-Tersoff potentials in atomistic simulations of InGaAsSb/GaAs. , 2008, , .		0
126	Self-assembling processes involved in the molecular beam epitaxy growth of stacked InAs/InP quantum wires. Nanotechnology, 2008, 19, 445601.	2.6	4

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127	Anisotropic spatial structure of deep acceptor states in GaAs and GaP. Physical Review B, 2008, 77, .	3.2	21
128	Structural properties of GaAsNâˆ•GaAs quantum wells studied at the atomic scale by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2008, 93, 083103.	3.3	20
129	Single-exciton spectroscopy of single Mn doped InAs quantum dots. Physical Review B, 2008, 78, .	3.2	29
130	Influence of an ultrathin GaAs interlayer on the structural properties of InAsâˆ•InGaAsPâˆ•InP (001) quantum dots investigated by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2008, 92, 083103.	3.3	19
131	Correlation lengths in stacked InAs quantum dot systems studied by cross-sectional scanning tunnelling microscopy. Nanotechnology, 2007, 18, 145403.	2.6	6
132	Double capping of molecular beam epitaxy grown InAsâˆ•InP quantum dots studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2007, 91, .	3.3	23
133	Cross-sectional scanning tunneling microscopy study on IIâ€“VI multilayer structures. Applied Physics Letters, 2007, 91, .	3.3	8
134	Suppression of InAsâˆ•GaAs quantum dot decomposition by the incorporation of a GaAsSb capping layer. Applied Physics Letters, 2007, 90, 213105.	3.3	85
135	Population Dynamics of Excitons in Silicon Nanocrystals Structures under Strong Optical Excitation. Advanced Materials Research, 2007, 31, 196-198.	0.3	0
136	Oscillatory Persistent Currents in Self-Assembled Quantum Rings. Physical Review Letters, 2007, 99, 146808.	7.8	192
137	Atomic scale study of the impact of the strain and composition of the capping layer on the formation of InAs quantum dots. Journal of Applied Physics, 2007, 101, 081707.	2.5	48
138	Theory of electron energy spectrum and Aharonov-Bohm effect in self-assembled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mi mathvariant="normal">As</mml:mi></mml:mrow></mml:math>quantum rings in GaAs. Physical Review B, 2007, 76, .	3.2	90
139	Oscillatory persistent currents in nano-volcanoes. AIP Conference Proceedings, 2007, , .	0.4	0
140	Warping a single Mn acceptor wavefunction by straining the GaAs host. Nature Materials, 2007, 6, 512-515.	27.5	65
141	Electronic and optical properties ofInAsâˆ•InPquantum dots on InP(100) andInP(311)Bsubstrates: Theory and experiment. Physical Review B, 2006, 74, .	3.2	67
142	<title>A 60 GHz microwave resonance investigation of shallowly formed InAs quantum dots embedded in GaAs</title>. , 2006, , .		1
143	Atomic-scale structure and formation of self-assembled In(Ga)As quantum rings. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 41-45.	2.7	27
144	Capping of InAs quantum dots grown on (311)B InP studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2006, 89, 023119.	3.3	24

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145	Formation of InAs quantum dots and wetting layers in GaAs and AlAs analyzed by cross-sectional scanning tunneling microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 236-240.	2.7	26
146	Excited states of ring-shaped (InGa)As quantum dots in aGaAsâˆ•(AlGa)Asquantum well. Physical Review B, 2005, 72, .	3.2	13
147	Modeling of the Magnetization Behavior of Realistic Self-Organized InAs/GaAs Quantum Craters as Observed with Cross-Sectional STM. AIP Conference Proceedings, 2005, , .	0.4	5
148	Formation of InAs wetting layers studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2005, 87, 111903.	3.3	57
149	Spatial Structure of Mn-Mn Acceptor Pairs in GaAs. Physical Review Letters, 2005, 95, 256402.	7.8	38
150	(In,Ga)As sidewall quantum wires on shallow-patterned InP (311)A. Journal of Applied Physics, 2005, 97, 063510.	2.5	3
151	Relaxation of a strained quantum well at a cleaved surface. Part II: Effect of cubic symmetry. Journal of Applied Physics, 2005, 98, 053504.	2.5	3
152	Atomic-scale structure and photoluminescence of InAs quantum dots in GaAs and AlAs. Physical Review B, 2005, 72, .	3.2	71
153	Atomic-scale structure of self-assembled In(Ga)As quantum rings in GaAs. Applied Physics Letters, 2005, 87, 131902.	3.3	126
154	Capping process of InAsâˆ•GaAs quantum dots studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2004, 85, 5697-5699.	3.3	103
155	Low-temperature electron mobilities due to ionized-impurity scattering in multisubband two-dimensional semiconductor systems. Physical Review B, 2004, 70, .	3.2	4
156	Spatial Structure of an Individual Mn Acceptor in GaAs. Physical Review Letters, 2004, 92, 216806.	7.8	185
157	Formation of columnar (In,Ga)As quantum dots on GaAs(100). Applied Physics Letters, 2004, 85, 2771-2773.	3.3	45
158	Semiconductor Nanostructures for Infrared Applications. Solid State Phenomena, 2004, 99-100, 99-108.	0.3	1
159	High-field magnetotransport in a two-dimensional electron gas in quantizing magnetic fields and intense terahertz laser fields. Journal of Physics Condensed Matter, 2004, 16, 89-101.	1.8	23
160	Scanning tunneling spectroscopy on organic semiconductors: Experiment and model. Physical Review B, 2004, 70, .	3.2	38
161	Composition profiling at the atomic scale in IIIâ€“V nanostructures by cross-sectional STM. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 526-532.	2.7	11
162	Spatial correlation effects in the charged impurity distribution on the electronic properties of Î´-doped structures. Physica Status Solidi (B): Basic Research, 2003, 237, 405-425.	1.5	3

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163	On the experimental data processing of magnetoresistance oscillations in two-dimensional electron gas. Semiconductors, 2003, 37, 160-164.	0.5	1
164	Relating Substitution to Single-Chain Conformation and Aggregation in Poly(p-phenylene Vinylene) Films. Nano Letters, 2003, 3, 1191-1196.	9.1	49
165	Spatially resolved scanning tunneling luminescence on self-assembled InGaAs/GaAs quantum dots. Applied Physics Letters, 2003, 83, 290-292.	3.3	10
166	Annealing of InGaAlAs digital alloy studied with scanning-tunneling microscopy and filled-states topography. Applied Physics Letters, 2003, 82, 1191-1193.	3.3	8
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